



A Product Line of Diodes Incorporated



## 60V PNP MEDIUM POWER LOW SATURATION TRANSISTOR IN SOT223

#### **Features**

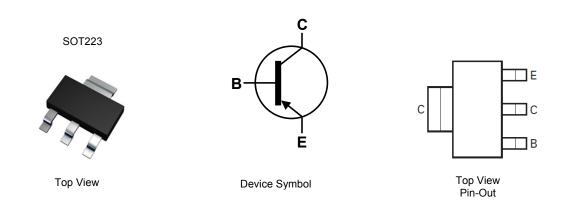
- BV<sub>CEO</sub> > -60V
- I<sub>C</sub> = -5.5A High Continuous Collector Current
- I<sub>CM</sub> = -15A Peak Pulse Current
- Low Saturation Voltage V<sub>CE(sat)</sub> < -70mV @ -1A</li>
- R<sub>SAT</sub> = 39mΩ for a Low Equivalent On-Resistance
- hFE Specified Up to -10A for a High Gain Hold Up
- Complementary NPN Type: ZX5T851G
- Lead-Free Finish; RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 <sup>(23)</sup>
- Weight: 0.112 grams (approximate)

### **Applications**

- DC-DC converters
- MOSFET & IGBT gate drivers
- Charging circuits
- Power switches
- Motor control



### Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZX5T951GTA	X5T951	7	12	1,000
ZX5T951GTC	X5T951	13	12	4,000

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

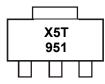
2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com

## **Marking Information**

Notes:



X5T951 = Product type Marking Code





#### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-100	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-60	V
Emitter-Base Voltage	V <sub>EBO</sub>	-7	V
Continuous Collector Current	Ι <sub>C</sub>	-5.5	А
Peak Pulse Current	I <sub>CM</sub>	-15	А

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)		3.0 24	W	
Linear derating factor	(Note 6)	PD	1.6 12.8	mW /°C	
Thermal Resistance, Junction to Ambient	(Note 5)	R <sub>0JA</sub>	42		
Thermal Resistance, Junction to Amblent	(Note 6)	$R_{ heta JA}$	78	°C/W	
Thermal Resistance Junction to Lead	(Note 7)	R <sub>θJL</sub>	10.48		
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C		

## ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	С

5. For a device surface mounted on 52mm x 52mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is Notes: measured when operating in a steady-state condition.

6. Same as note (5), except the device is surface mounted on 25mm x 25mm with 1oz copper.

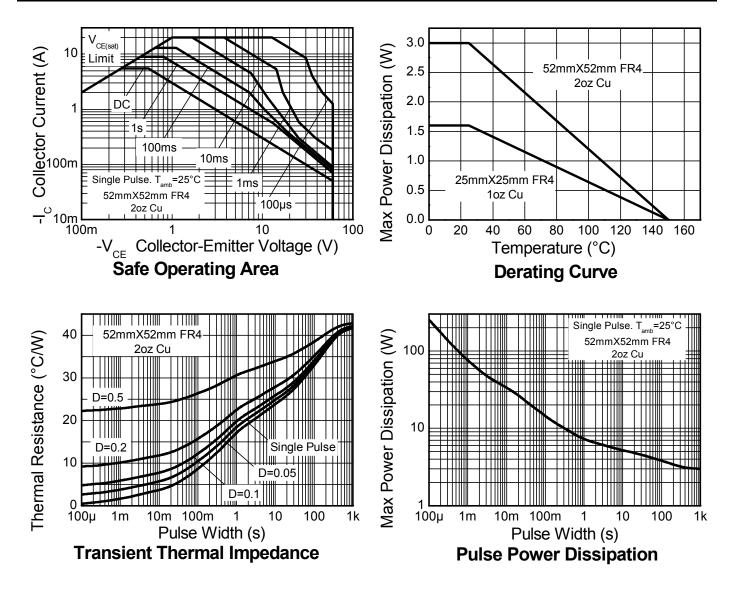
7. Thermal resistance from junction to solder-point (at the end of the collector lead).

8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.





# Thermal Characteristics and Derating Information







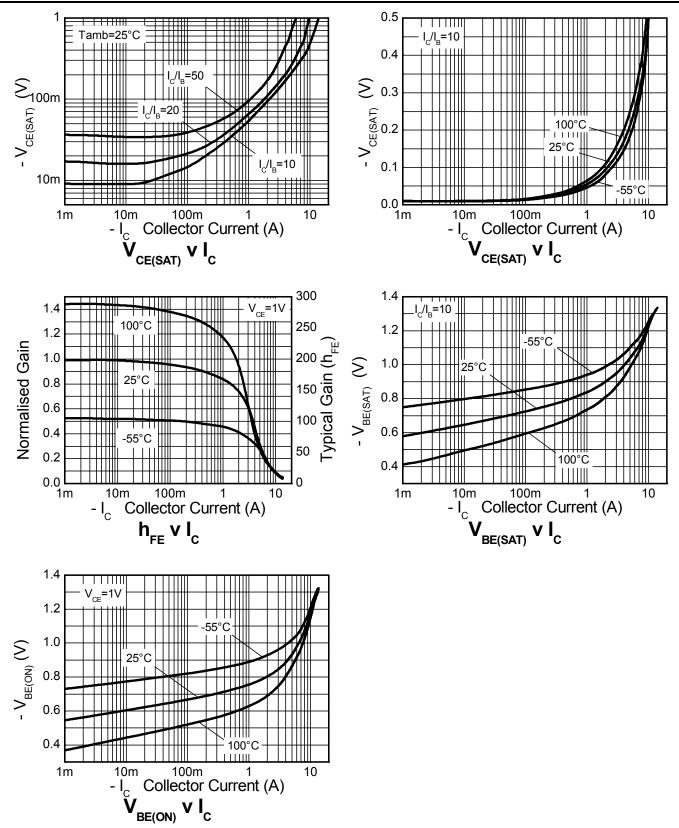
Electrical Characteristics (@T <sub>A</sub> = +2	5°C, unless otherwis	e specified.	.)			
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-100	-120	-	V	I <sub>C</sub> = -100μA
Collector-Emitter Breakdown Voltage	BV <sub>CER</sub>	-100	-120	-	V	I <sub>C</sub> = -1μA, RB ≤ 1kΩ
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	-60	-80	-	V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-7	-8.1	-	V	I <sub>E</sub> = -100μA
Collector-Base Cutoff Current	I <sub>CBO</sub>	-	<1 -	-20 -0.5	nA μA	V <sub>CB</sub> = -80V V <sub>CB</sub> = -80V, T <sub>A</sub> = +100°C
Collector-Emitter Cutoff Current	l <sub>CER</sub> R ≤ 1kΩ	-	<1 -	-20 -0.5	nA μA	V <sub>CB</sub> = -80V V <sub>CB</sub> = -80V, T <sub>A</sub> = +100°C
Emitter Cutoff Current	I <sub>EBO</sub>	-	<1	-10	nA	$V_{EB} = -6V$
		100	250	-		I <sub>C</sub> = -10mA, V <sub>CE</sub> = -1V
Static Forward Current Transfer Ratio (Note 9)	Ŀ	100	200	300		I <sub>C</sub> = -2A, V <sub>CE</sub> = -1V
Static Forward Current Transfer Ratio (Note 9)	h <sub>FE</sub>	45 90 - I <sub>C</sub> = -5A, V <sub>CE</sub> =		I <sub>C</sub> = -5A, V <sub>CE</sub> = -1V		
		10	25	-		I <sub>C</sub> = -10A, V <sub>CE</sub> = -1V
	V <sub>CE(sat)</sub>	-	-15	-25		I <sub>C</sub> = -100mA, I <sub>B</sub> = -10mA
Collector Emitter Seturation Valtage (Note 0)		-	-55	-70	mV	I <sub>C</sub> = -1A, I <sub>B</sub> = -100mA
Collector-Emitter Saturation Voltage (Note 9)		-	-90	-120	IIIV	I <sub>C</sub> = -2A, I <sub>B</sub> = -200mA
		-	-195	-250		I <sub>C</sub> = -5A, I <sub>B</sub> = -500mA
Base-Emitter Saturation Voltage (Note 9)	V <sub>BE(sat)</sub>	-	-1030	-1150	mV	I <sub>C</sub> = -5A, I <sub>B</sub> = -500mV
Base-Emitter Turn-On Voltage (Note 9)	V <sub>BE(on)</sub>	-	-920	-1020	mV	I <sub>C</sub> = -5A, V <sub>CE</sub> = -1V
Output Capacitance (Note 9)	C <sub>obo</sub>	-	48	-	pF	V <sub>CB</sub> = -10V. f = 1MHz
Transition Frequency	f <sub>T</sub>	-	120	-	MHz	V <sub>CE</sub> = -10V, I <sub>C</sub> = -100mA f = 50MHz
Switching Time	t <sub>on</sub>	-	39	-	20	V <sub>CC</sub> = -10V, I <sub>C</sub> = -1A
Switching Time	t <sub>off</sub>	-	370	-	ns	I <sub>B1</sub> = -I <sub>B2</sub> = -100mA

Notes: 9. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%





# Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

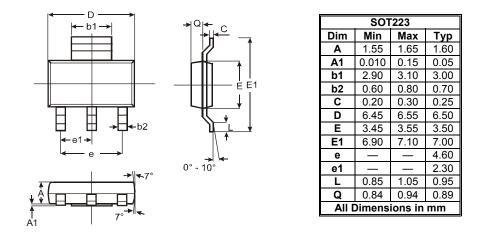






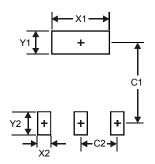
# **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
X1	3.3
X2	1.2
Y1	1.6
Y2	1.6
C1	6.4
C2	2.3





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